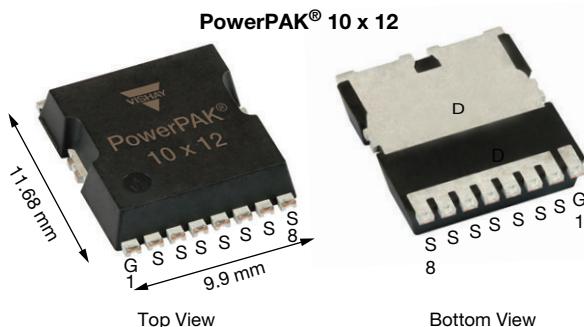


## N-Channel 100 V (D-S) MOSFET



### FEATURES

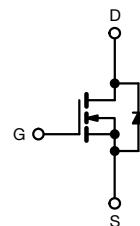
- TrenchFET® Gen V power MOSFET
- Leadership  $R_{DS(on)}$  minimizes power loss from conduction
- 100 %  $R_g$  and UIS tested
- Standard level FET
- Enhance power dissipation and lower  $R_{thJC}$
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
**HALOGEN**  
**FREE**

### APPLICATIONS

- Synchronous rectification
- Automation
- OR-ing and hot swap switch
- Power supplies
- Motor drive control
- Battery management



N-Channel MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	100
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.0014
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5$ V	0.0016
$Q_g$ typ. (nC)	131
$I_D$ (A) <sup>a</sup>	417
Configuration	Single

### ORDERING INFORMATION

Package	PowerPAK® 10 x 12
Lead (Pb)-free and halogen-free	SiJK5100E-T1-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	100	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current ( $T_J = 175$ °C)	$I_D$	417	A
		295	
		74 b, c	
		52 b, c	
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	700	
Continuous source-drain diode current	$I_S$	487	
		15 b, c	
Single pulse avalanche current	$I_{AS}$	65	mJ
Single pulse avalanche energy	$E_{AS}$	214	
Maximum power dissipation	$P_D$	536	W
		268	
		17 b, c	
		8.3 b, c	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +175	°C
Soldering recommendations (peak temperature) <sup>c</sup>		260	

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	$R_{thJA}$	6.3	9	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	0.21	0.28	

#### Notes

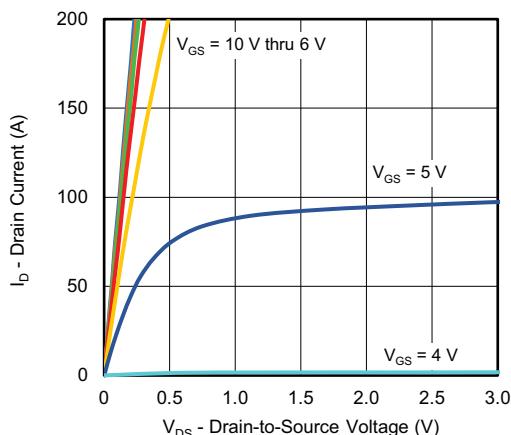
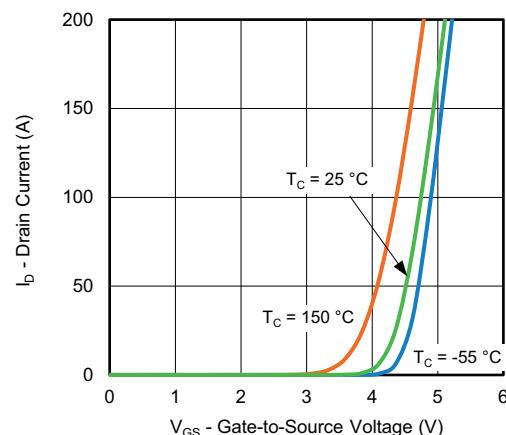
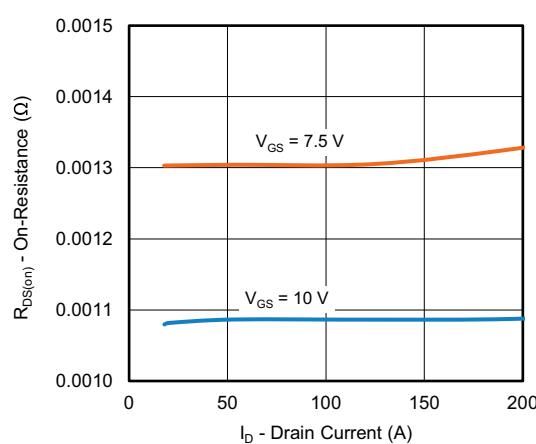
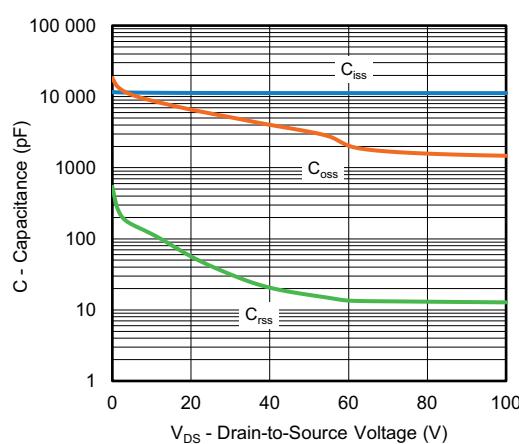
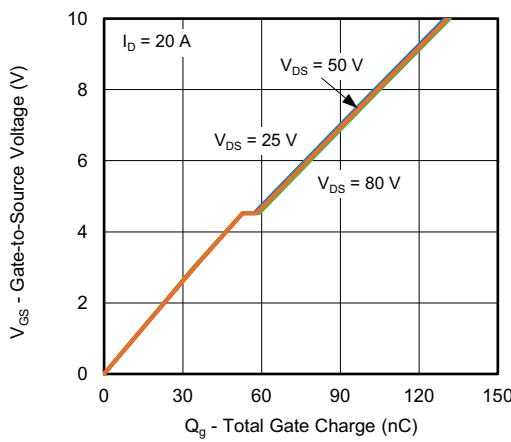
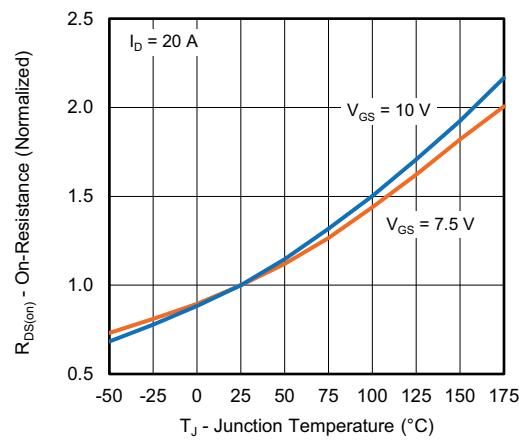
- $T_C = 25$  °C
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- See solder profile ([www.vishay.com/doc?773257](http://www.vishay.com/doc?773257)). The PowerPAK 10 x 12 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 39 °C/W

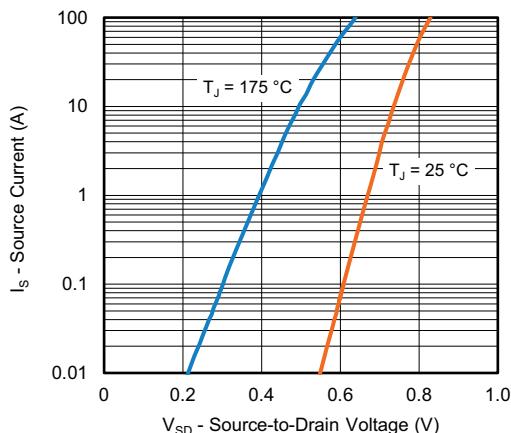
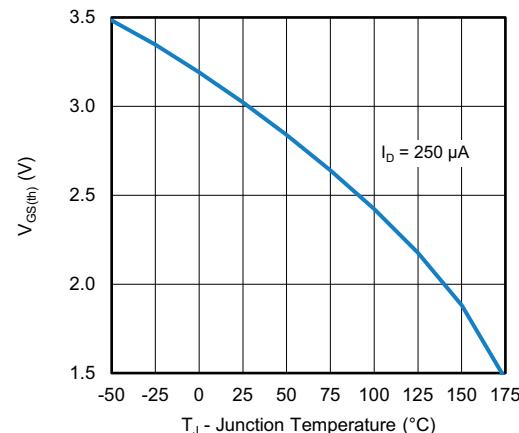
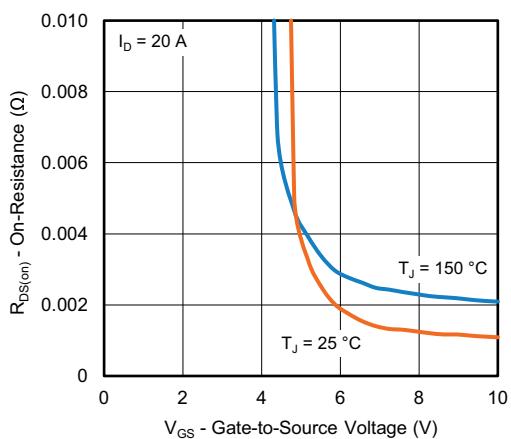
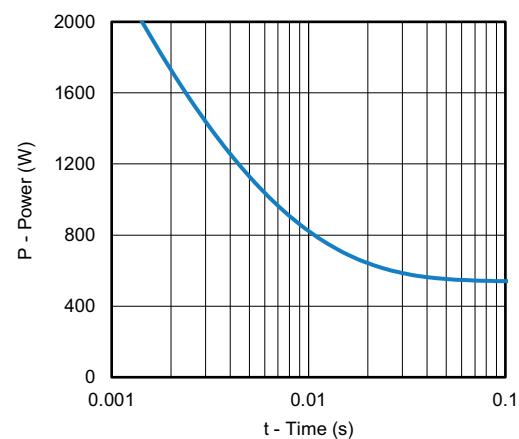
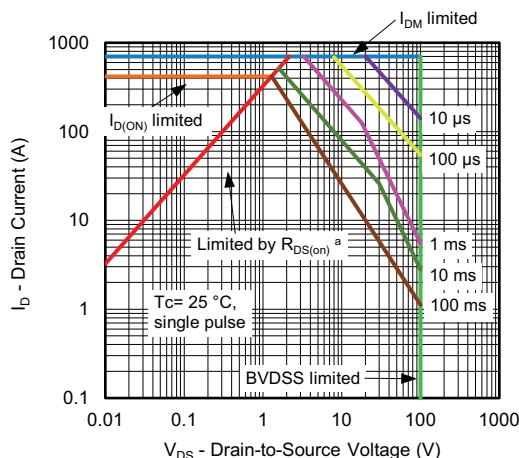
<b>SPECIFICATIONS</b> ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	100	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 10 \text{ mA}$	-	55	-	$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ temperature coefficient	$\Delta V_{GS(\text{th})}/T_J$	$I_D = 250 \mu\text{A}$	-	-8	-	
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	2	-	4	V
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 80 \text{ V}$ , $V_{GS} = 0 \text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 80 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 55^\circ\text{C}$	-	-	10	
Drain-source on-state resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$ , $I_D = 80 \text{ A}$	-	0.00110	0.00140	$\Omega$
		$V_{GS} = 7.5 \text{ V}$ , $I_D = 80 \text{ A}$	-	0.00125	0.00160	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 25 \text{ V}$ , $I_D = 100 \text{ A}$	-	245	-	S
<b>Dynamic</b> <sup>b</sup>						
Input capacitance	$C_{iss}$	$V_{DS} = 50 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	-	11 480	-	$\text{pF}$
Output capacitance	$C_{oss}$		-	3210	-	
Reverse transfer capacitance	$C_{rss}$		-	17	-	
Total gate charge	$Q_g$	$V_{DS} = 50 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 20 \text{ A}$	-	131	200	$\text{nC}$
Gate-source charge	$Q_{gs}$		-	53	-	
Gate-drain charge	$Q_{gd}$		-	5.3	-	
Total gate charge	$Q_g$	$V_{DS} = 50 \text{ V}$ , $V_{GS} = 7.5 \text{ V}$ , $I_D = 20 \text{ A}$	-	97.4	146	
Output charge	$Q_{oss}$	$V_{DS} = 50 \text{ V}$ , $V_{GS} = 0 \text{ V}$	-	330	-	
Gate resistance	$R_g$	$f = 1 \text{ MHz}$	0.2	0.8	1.6	$\Omega$
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD} = 50 \text{ V}$ , $R_L = 5 \Omega$ , $I_D \geq 10 \text{ A}$ , $V_{GEN} = 10 \text{ V}$ , $R_g = 1 \Omega$	-	32	65	$\text{ns}$
Rise time	$t_r$		-	15	30	
Turn-off delay time	$t_{d(\text{off})}$		-	54	110	
Fall time	$t_f$		-	35	70	
Turn-on delay time	$t_{d(\text{on})}$		-	41	80	$\text{ns}$
Rise time	$t_r$	$V_{DD} = 20 \text{ V}$ , $R_L = 5 \Omega$ , $I_D \geq 10 \text{ A}$ , $V_{GEN} = 7.5 \text{ V}$ , $R_g = 1 \Omega$	-	18	35	
Turn-off delay time	$t_{d(\text{off})}$		-	47	95	
Fall time	$t_f$		-	35	70	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	$T_C = 25^\circ\text{C}$	-	-	487	$\text{A}$
Pulse diode forward current	$I_{SM}$		-	-	700	
Body diode voltage	$V_{SD}$	$I_S = 10 \text{ A}$ , $V_{GS} = 0 \text{ V}$	-	0.7	1.1	V
Body diode reverse recovery time	$t_{rr}$	$I_F = 10 \text{ A}$ , $\text{di}/\text{dt} = 100 \text{ A}/\mu\text{s}$ , $T_J = 25^\circ\text{C}$	-	140	280	$\text{ns}$
Body diode reverse recovery charge	$Q_{rr}$		-	360	720	
Reverse recovery fall time	$t_a$		-	61	-	$\text{ns}$
Reverse recovery rise time	$t_b$		-	79	-	

**Notes**

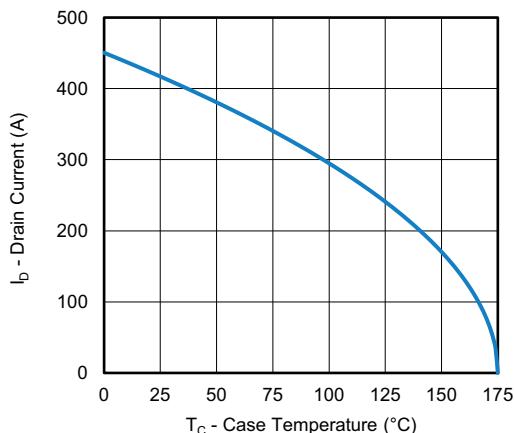
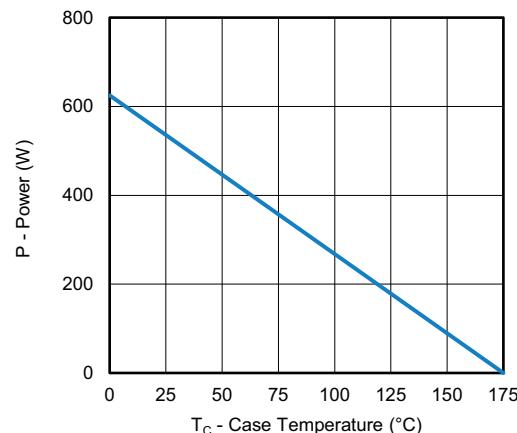
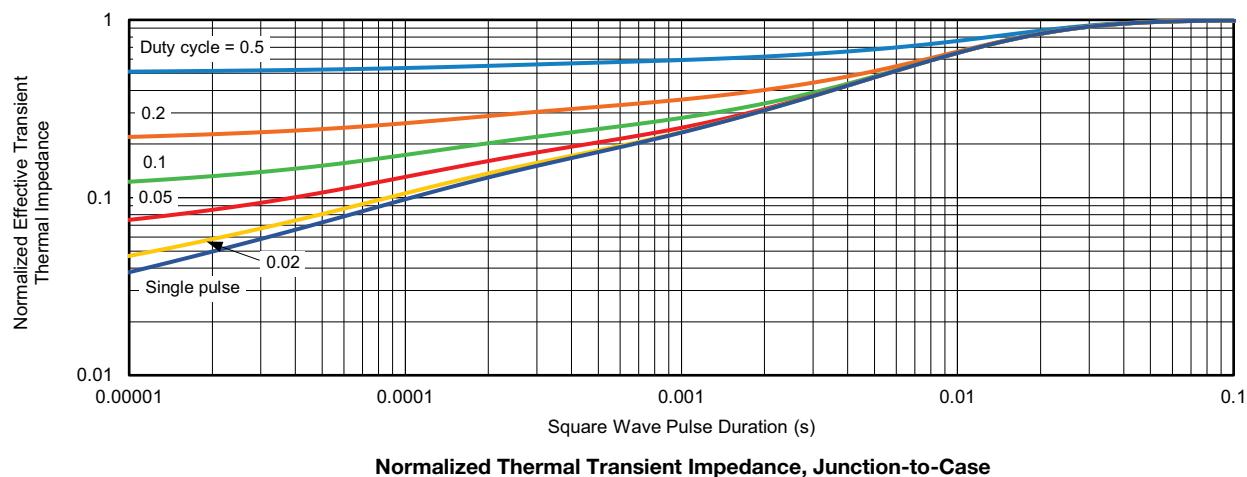
- Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$
- Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current and Gate Voltage**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Source-Drain Diode Forward Voltage**

**Threshold Voltage**

**On-Resistance vs. Gate-to-Source Voltage**

**Single Pulse Power, Junction-to-Case**

**Safe Operating Area, Junction-to-Ambient**
**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

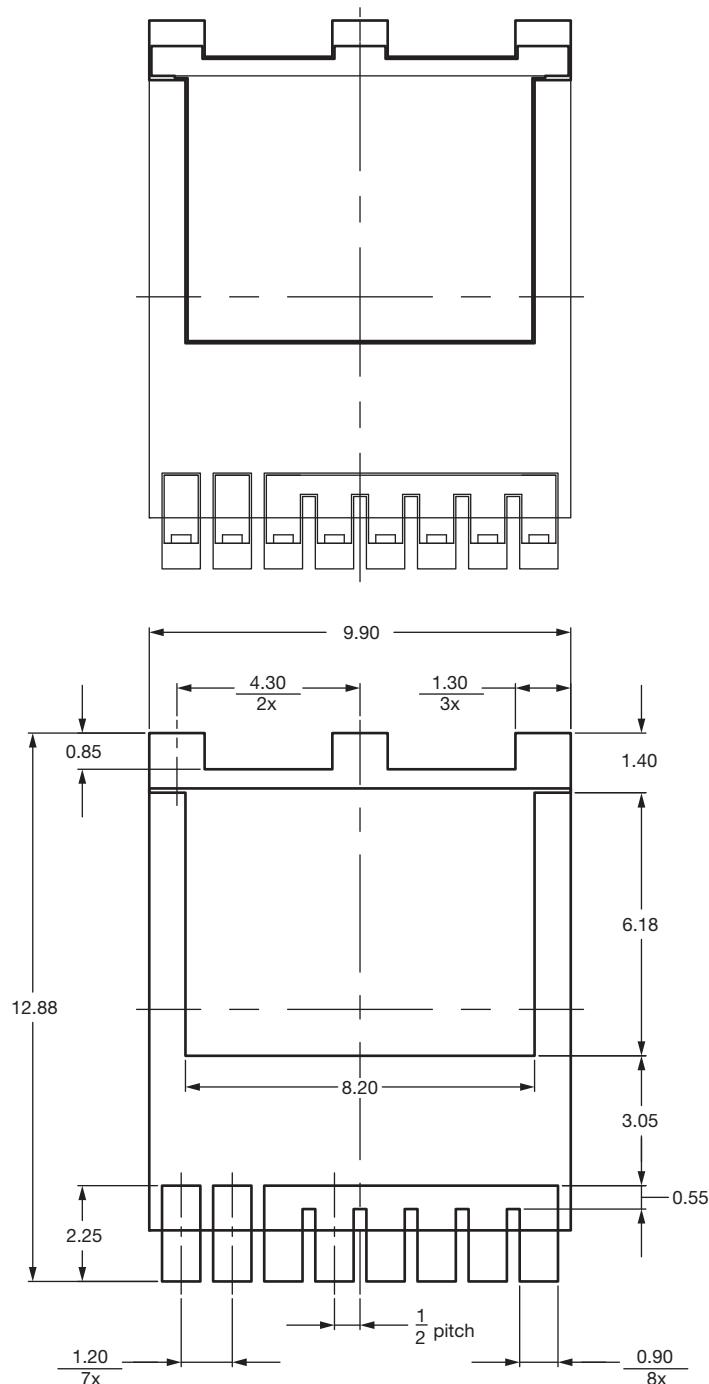
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Current Derating <sup>a</sup>**

**Power, Junction-to-Case**

**Normalized Thermal Transient Impedance, Junction-to-Case**
**Note**

a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

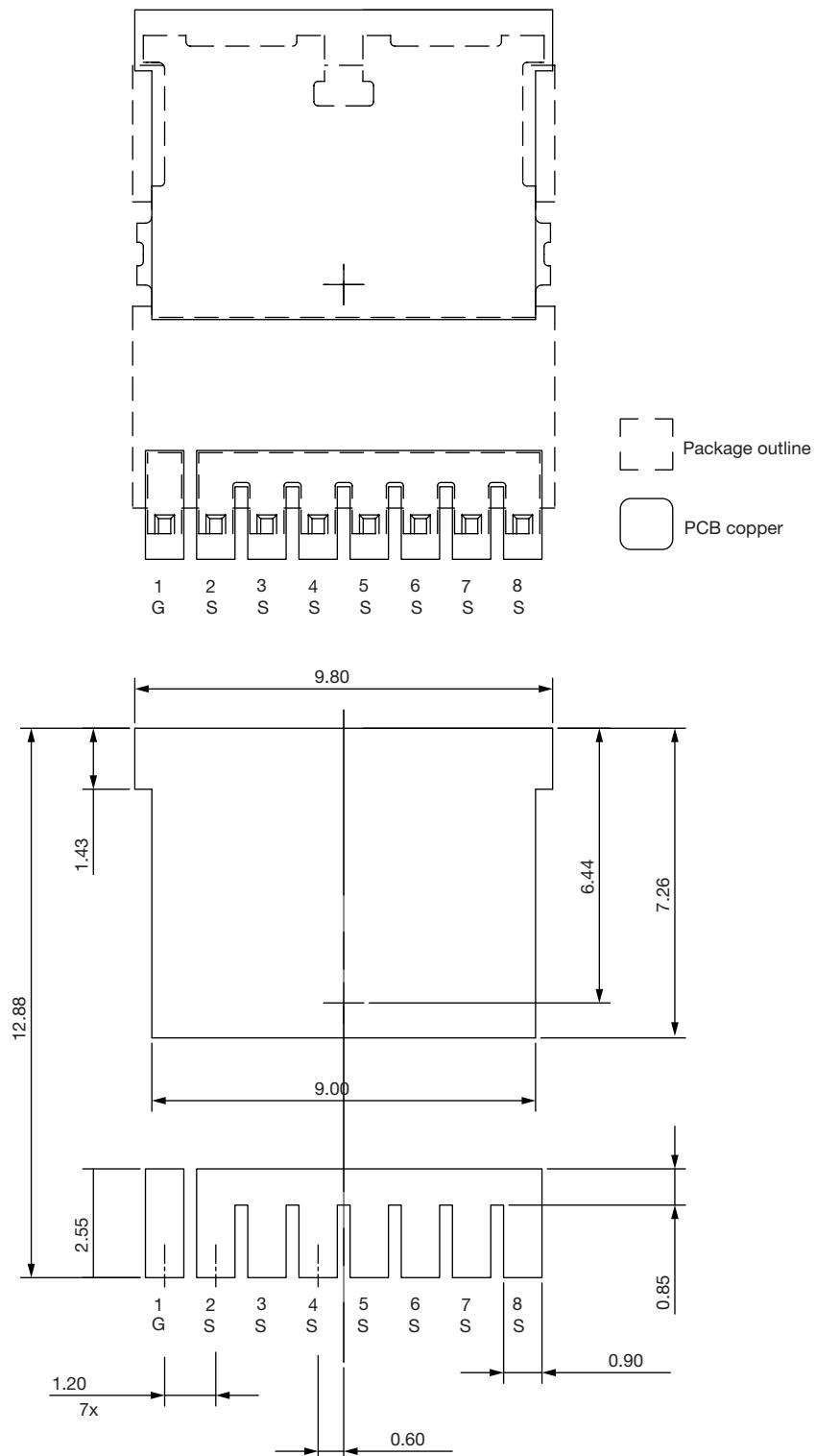
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## Recommended Land Pattern PowerPAK® 10 x 12

### PowerPAK® 10 x 12-1


**Note**

- Dimensions in mm

**PowerPAK® 10 x 12-2**

**Note**

- Dimensions in mm

ECN: S25-0975-Rev. A, 18-Aug-2025

DWG: 3037

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